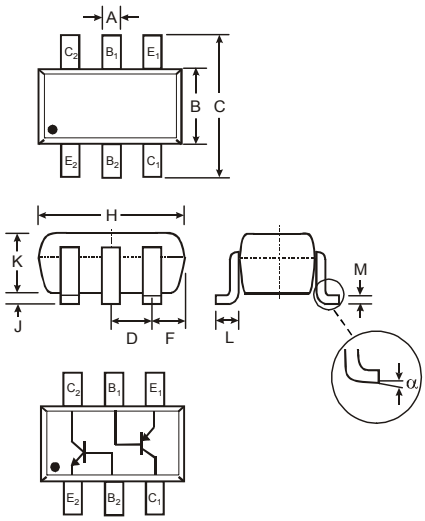
MMDT3946

COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Complementary Pair One 3904-Type NPN
  One 3906-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 4 and 5)**



E1, B1, C1 = PNP3906 Section
E2, B2, C2 = NPN3904 Section

SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: K46 - See Page 5
- Ordering & Date Code Information: See Page 5
- Weight: 0.006 grams (approximate)

Maximum Ratings, NPN 3904 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	NPN 3904 Section	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I_C	200	mA
Power Dissipation (Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Maximum Ratings, PNP 3906 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	PNP 3906 Section	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I_C	-200	mA
Power Dissipation (Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. Maximum combined dissipation.
3. No purposefully added lead.
4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
5. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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Electrical Characteristics, NPN 3904 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	I_C = 10μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5.0	6.0	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
Base Cutoff Current	I_{BL}	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	40 70 100 60 30	— — 300 — —	—	I_C = 100μA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 50mA, V_{CE} = 1.0V I_C = 100mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.20 0.30	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.65 —	0.85 0.95	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	8.0	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	10	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.5	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = 20V, I_C = 20mA, f = 100MHz
Noise Figure	NF	—	5.0	dB	V_{CE} = 5.0V, I_C = 100μA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = 3.0V, I_C = 10mA, $V_{BE(off)}$ = - 0.5V, I_{B1} = 1.0mA
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	200	ns	V_{CC} = 3.0V, I_C = 10mA, I_{B1} = I_{B2} = 1.0mA
Fall Time	t_f	—	50	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.

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Electrical Characteristics, PNP 3906 Section @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	I_C = -10μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	I_E = -10μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
Base Cutoff Current	I_{BL}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	60 80 100 60 30	— — 300 — —	—	I_C = -100μA, V_{CE} = -1.0V I_C = -1.0mA, V_{CE} = -1.0V I_C = -10mA, V_{CE} = -1.0V I_C = -50mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65 —	-0.85 -0.95	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.5	pF	V_{CB} = -5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	10	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	2.0	12	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	10	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	V_{CE} = -20V, I_C = -10mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V_{CE} = -5.0V, I_C = -100μA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = -3.0V, I_C = -10mA, $V_{BE(off)}$ = 0.5V, I_{B1} = -1.0mA
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	225	ns	V_{CC} = -3.0V, I_C = -10mA, I_{B1} = I_{B2} = -1.0mA
Fall Time	t_f	—	75	ns	

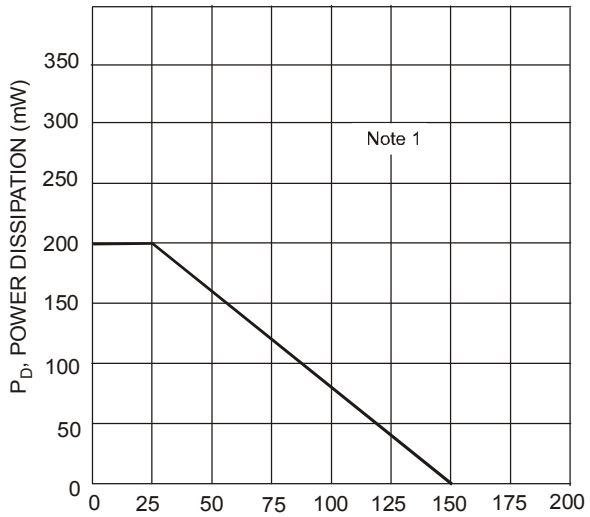


Fig. 1, Max Power Dissipation vs. Ambient Temperature (Total Device)

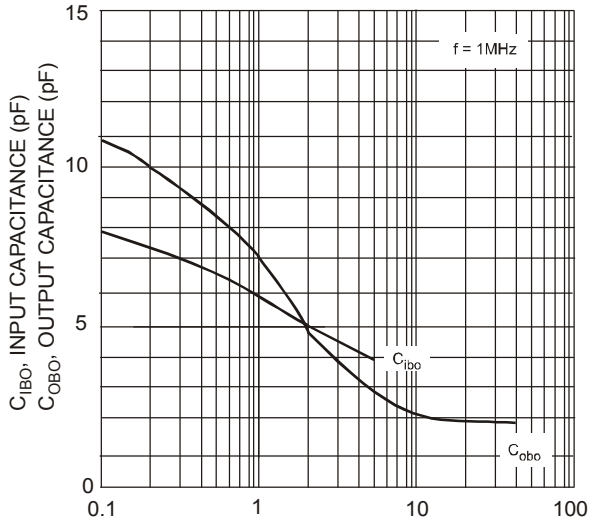


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage (NPN-3904)

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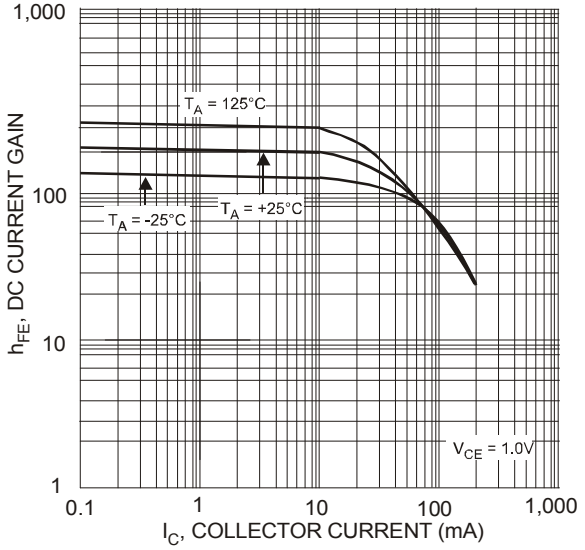


Fig. 3, Typical DC Current Gain vs. Collector Current (NPN-3904)

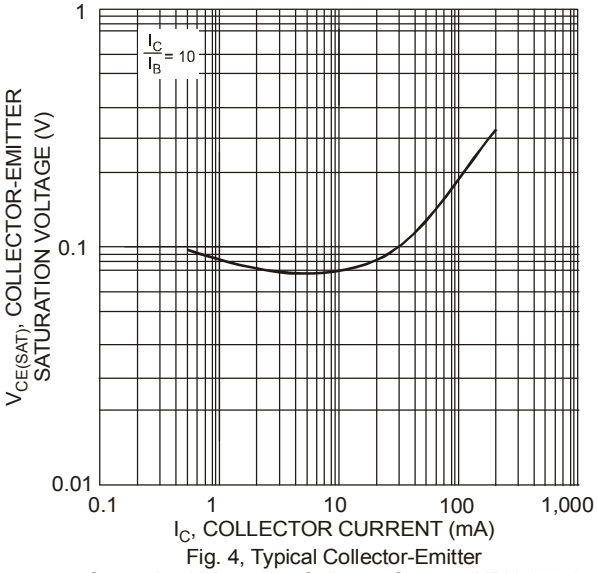


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current (NPN-3904)

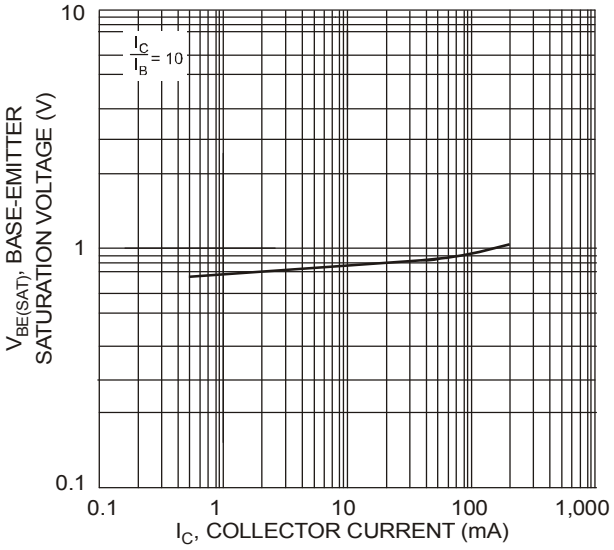


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current (NPN-3904)

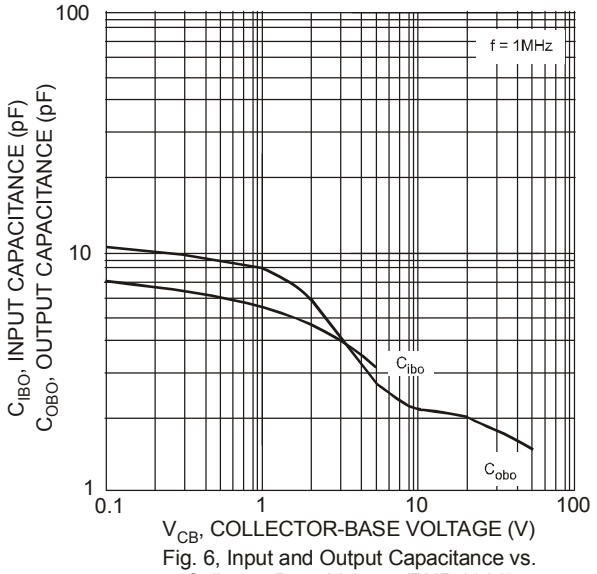


Fig. 6, Input and Output Capacitance vs. Collector-Base Voltage (PNP-3906)

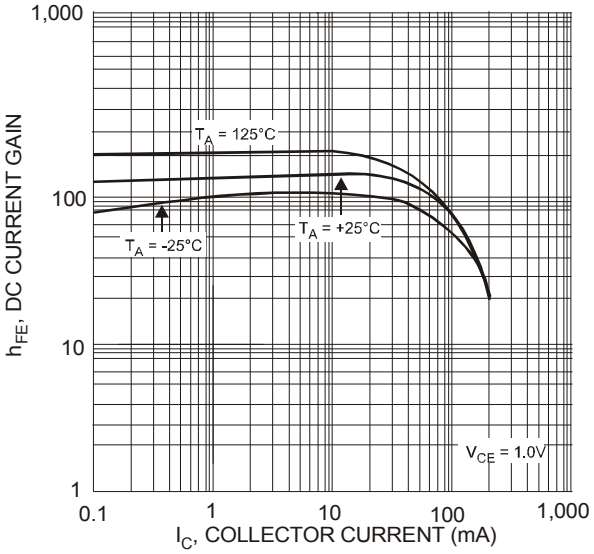


Fig. 7, Typical DC Current Gain vs. Collector Current (PNP-3906)

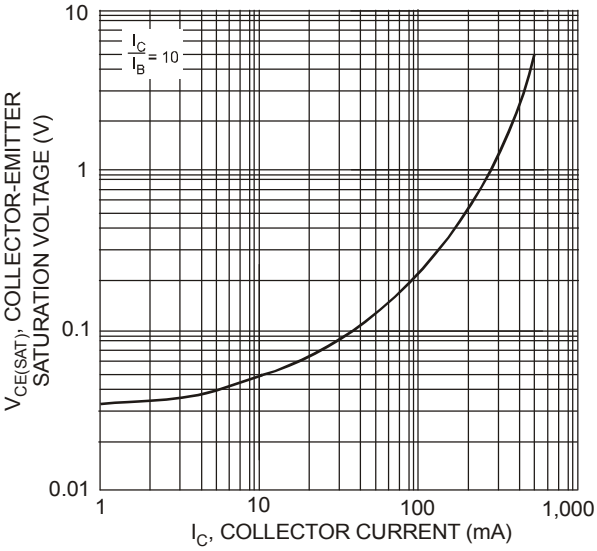


Fig. 8, Typical Collector-Emitter Saturation Voltage vs. Collector Current (PNP-3906)

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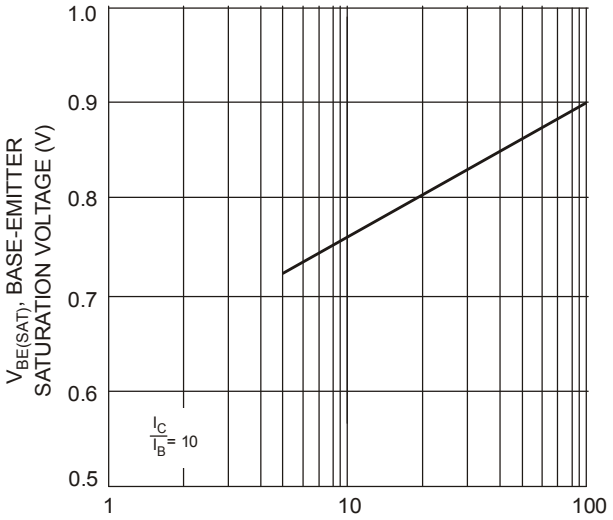


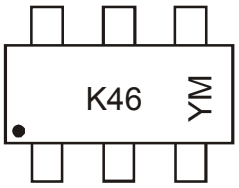
Fig. 9, Typical Base-Emitter
Saturation Voltage vs. Collector Current (PNP-3906)

Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT3946-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K46 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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